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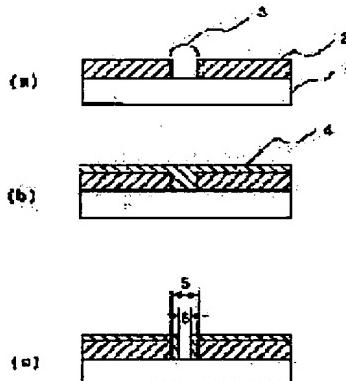
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(54) PATTERN FORMING METHOD

(57)Abstract:

PURPOSE: To enable the formation of groove patterns and hole patterns to effectively smaller sizes and the formation of the fine patterns below the resolution threshold of lithography.

CONSTITUTION: The patterns are formed of a resist 2 contg. an acid generating agent which generates an acid by irradiation with energy rays. A chemical amplification type resist 4 which reacts to a negative type by utilizing the sensitization reaction of the acid is deposited thereon. The resist is subjected to a heat treatment in this state. The acid in the resist 2 is diffused at a specified depth to the resist 4 by the stage and is brought into reaction to the negative type. The resist is then



subjected to development processing, by which the excess resist not reacting to the negative type is removed.

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